Features

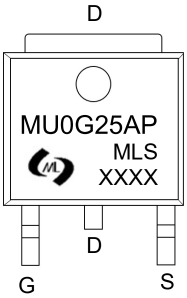
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
-60V	53mΩ@-10V 70mΩ@-4.5V	-25A

Application

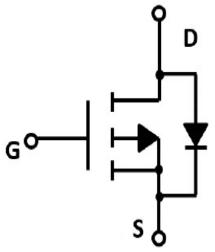
- PWM applications
- Power management
- Load switch



MU0G25AP: Device code
XXXX : Code

Marking and pin assignment

TO-252 Top view



Schematic diagram

Pb-Free RoHS Halogen-Free

Absolute Maximum Ratings (TA=25℃unless otherwise noted)				
Symbol	**Parameter**		**Rating**	**Unit**
Common Ratings (TC=25°C Unless Otherwise Noted)				
V_{DS}	Drain-Source Breakdown Voltage		-60	V
V_{GS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	Tc=25°C	-25	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested	Tc=25°C	-110	A
I_D	Continuous Drain Current	Tc=25°C	-25	A
P_D	Maximum Power Dissipation	Tc=25°C	80	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient		50	°C/W

Ordering Information (Example)						
Type	**Package**	**Marking**	**Minimum Package(pcs)**	**Inner Box Quantity(pcs)**	**Outer Carton Quantity(pcs)**	**Delivery Mode**
MU0G25AP	TO-252	MU0G25AP	2,500	5,000	35,000	13"reel

Electrical Characteristics (TJ=25℃ unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$BV_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V，I_D=-250μA	-60	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-60V，V_{GS}=0V	--	--	-1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V，V_{DS}=0V	--	--	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}，I_D=-250μA	-1.0	-1.7	-2.5	V
$R_{DS(on)}$	Drain-Source On-State Resistance	V_{GS}=-10V，I_D=-20A	--	43	53	mΩ
		V_{GS}=-4.5V，I_D=-10A	--	50	70	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C_{ISS}	Input Capacitance	V_{DS}=-30V，V_{GS}=0V， f=1MHz	--	1650	--	pF
C_{OSS}	Output Capacitance		--	95	--	pF
C_{RSS}	Reverse Transfer Capacitance		--	75	--	pF
Switching Characteristics						
Q_g	Total Gate Charge	V_{DS}=-30V，I_D=-20A， V_{GS}=-10V	--	30	--	nC
Q_{gs}	Gate Source Charge		--	3.5	--	nC
Q_{gd}	Gate Drain Charge		--	7.7	--	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=-30V，I_D=-20A， V_{GS}=-10V，R_G=3Ω	--	11	--	nS
t_r	Turn-on Rise Time		--	14	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	33	--	nS
t_f	Turn-Off Fall Time		--	13	--	nS
Source- Drain Diode Characteristics						
V_{SD}	Forward on voltage	Tj=25℃，Is=-10A	--	--	-1.2	V

Typical Operating Characteristics

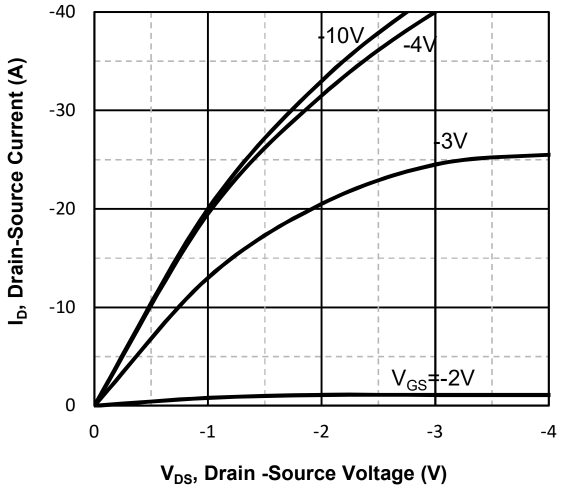


Fig1. Typical Output Characteristics

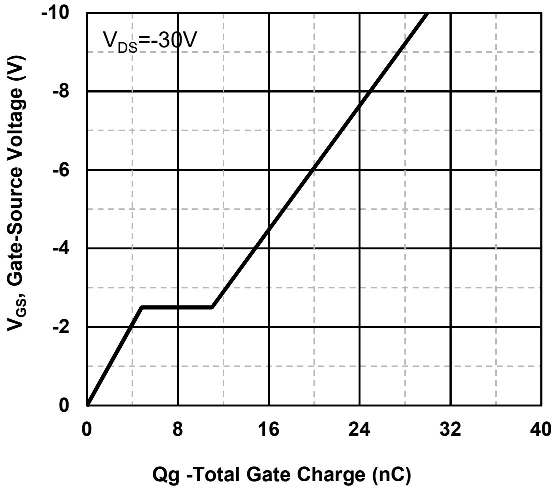


Fig2. Typical Gate Charge Vs.Gate-Source Voltage

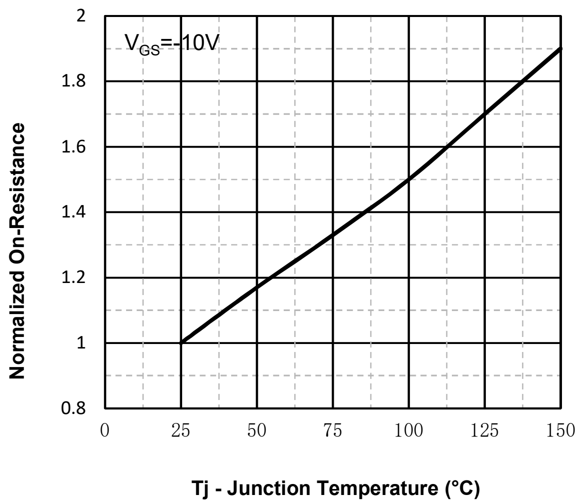


Fig3. Normalized On-Resistance Vs. Temperature

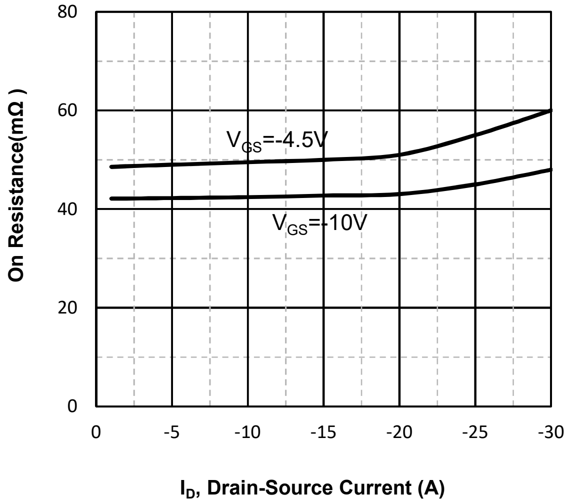


Fig4. Drain-Source on Resistance Vs.Drain-Source Current

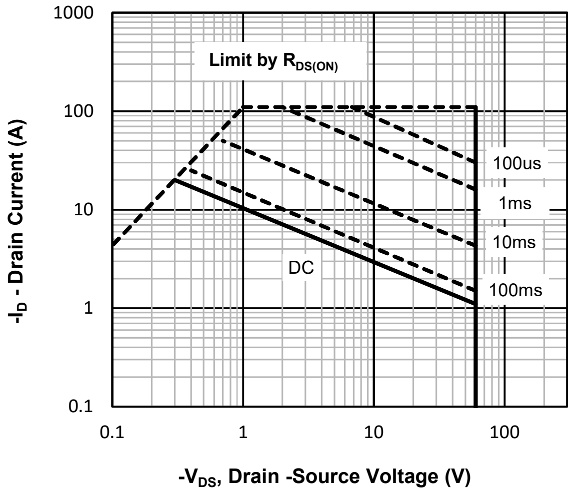


Fig5. Maximum Safe Operating Area

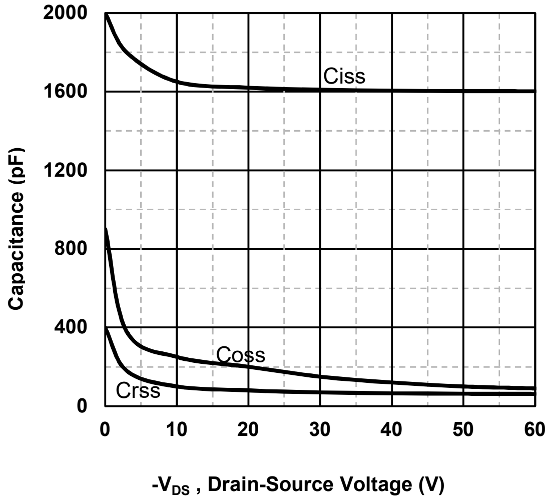
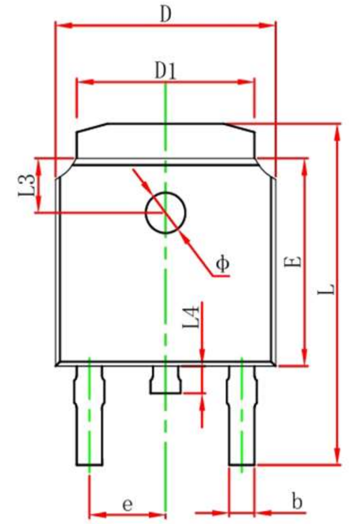
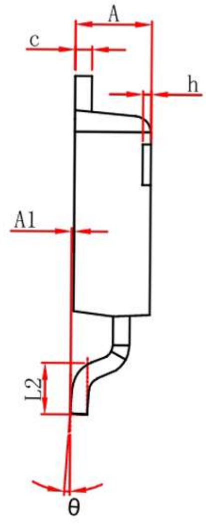
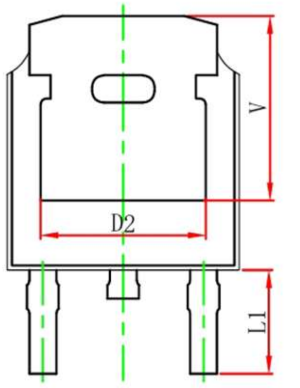


Fig6 Typical Capacitance Vs.Drain-Source Voltage

TO-252 Package information







Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.450	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.386	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	